Atty. Dkt. No. AMAT3577/DD/BCVD/JW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Application of:

Judy Huang

Serial No.: 09/336,525

Confirmation No.: 7748

Filed:

June 18, 1999

For:

Plasma Treatment to

Enhance Adhesion and to Minimize Oxidation of Carbon-Containing Layers

SEP 1 7 2001

Group Art Unit: 1762

Examiner:

M. Padgett

SEP 1 9 2001

Assistant Commissioner for Patents Washington, D.C. 20231

CERTIFICATE OF MAILING 37 CFR 1.8

I hereby certify that this correspondence is being deposited on September 12, 2001, with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

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Signature

Dear Sir:

RESPONSE TO OFFICE ACTION DATED JUNE 12, 2001

In response to the Office Action dated June 12, 2001, having a shortened statutory period for response set to expire on September 12, 2001, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below.

IN THE SPECIFICATIONS:

Please replace the paragraph at pg. 6 lines 8 –19, with the following paragraph:

B

The process regimes yield a SiC material having a dielectric constant of less than 7, preferably about 5 or less, and most preferably about 4.2 or less. To deposit such a SiC layer on a 200 mm wafer, a reactive gas source such as trimethylsilane is flown into a reaction chamber, such as a CENTURA® DxZTM chamber, without a substantial source of oxygen introduced into the reaction zone, the trimethylsilane flowing at a